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U.S. Department of Commerce Patent and Trademark Office	<b>APPLICANT</b> SUDA et al.	
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Information Disclosure Statement by Applicant		

## U.S. Patent Documents

Examiner Initial		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE

## Foreign Patent Documents

**Other Documents (Including Author, Title, Date Pertinent Pages, Etc.)**

		Norio Onojima et al., "High-Quality AlN by Initial Layer-by-Layer Growth on Surface-Controlled 4H-SiC(0001) Substrate", Jpn. J. Appl. Phys. Vol. 42, Part 2, No. 5A (May 1, 2003), pp. L445-L447.	
		N. Onojima et al., "Impact of SiC Surface Control on Initial Growth Mode and Crystalline Quality of AlN Grown by Molecular-Beam Epitaxy", Phys. Stat. Sol. (c) 0, No. 7 (2003), pp. 2529-2532/DOI 10.1002/pssc.200303358.	
		Jun Suda et al., "Either Step-Flow or Layer-by-Layer Growth for AlN on SiC (0001) Substrates", Mat. Res. Soc. Symp. Proc., Vol. 798 (2004), © Materials Research Society, pp. Y3.4.1-Y3.4.6.	
EXAMINER	/Matthew Song/	DATE CONSIDERED	09/14/2008

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